Abstracts

A Ku-Band Ultra Super Low-Noise Pseudomorphic Heterojunction FET in a Hollow Plastic PKG

T. Hirokawa, H. Negishi, Y. Nishimura, S. Ichikawa, J. Tanaka, T. Kimura, K. Watanabe and Y. Nashimoto. "A Ku-Band Ultra Super Low-Noise Pseudomorphic Heterojunction FET in a Hollow Plastic PKG." 1996 MTT-S International Microwave Symposium Digest 96.3 (1996 Vol. III [MWSYM]): 1603-1606.

This paper reports Ku-band ultra super low-noise pseudomorphic heterojunction FETs (pHJFETs) in a newly developed hollow plastic package. To achieve higher performance of pHJFETs, we employed further optimized epilayer structure with good interracial quality. The developed packaged HJFETs with 0.17 um T-shaped gate exhibited extremely low noise performance of 0.35 dB typical noise figure with 12.5 dB associated gain at 12 GHz.

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